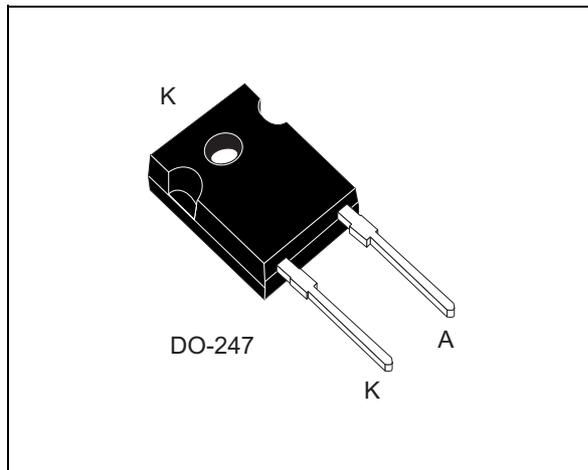


Turbo 2 ultrafast high voltage rectifier

Datasheet – production data


Description

The STTH30S12 is developed using ST's Turbo 2 1200 V technology. It is well-suited as a boost diode, especially for use in UPS.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	30 A
V_{RRM}	1200 V
t_{rr} (typ)	35 ns
V_F (typ)	1.9 V
T_j (max)	175 °C

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses

1 Characteristics

Table 2. Absolute ratings (limiting values at $T_j = 25\text{ °C}$, unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	1200	V
$I_{F(RMS)}$	Forward rms current	50	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 70\text{ °C}$	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}$	A
T_{stg}	Storage temperature range	-65 to +175	°C
T_j	Maximum operating junction temperature	175	°C

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	0.95	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$		15	μA
		$T_j = 150\text{ °C}$		60	600	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 30\text{ A}$		2.9	V
		$T_j = 150\text{ °C}$		1.9	2.7	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.8 \times I_{F(AV)} + 0.03 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
t_{rr}	Reverse recovery time	$T_j = 25\text{ °C}$	$I_F = 1\text{ A}, V_R = 30\text{ V},$ $di_F/dt = 200\text{ A}/\mu\text{s}$		35	50	ns
I_{RM}	Reverse recovery current	$T_j = 125\text{ °C}$	$I_F = 30\text{ A}, V_R = 600\text{ V},$ $di_F/dt = 200\text{ A}/\mu\text{s}$		17	24	A
S	Softness factor				2		
Q_{RR}	Reverse recovery charge				2900		nC

Figure 1. Average forward power dissipation versus average forward current

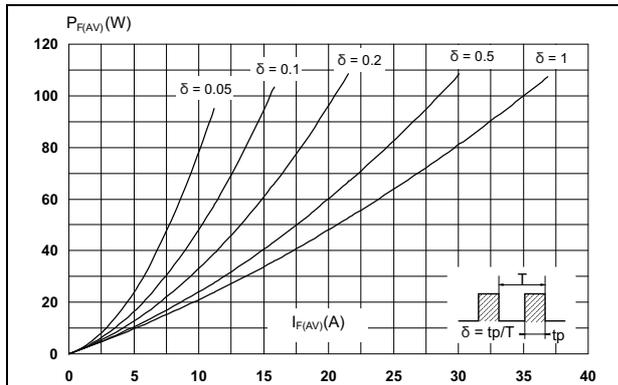


Figure 2. Forward voltage drop versus forward current (typical values)

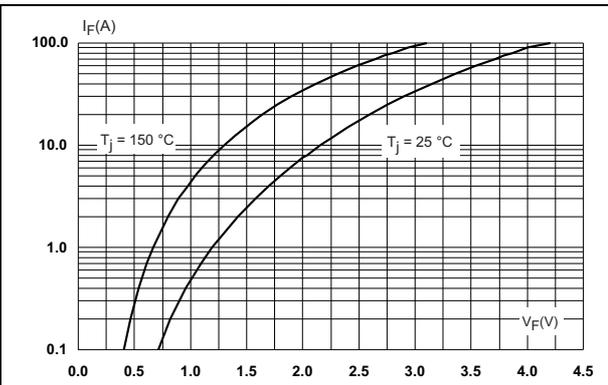


Figure 3. Forward voltage drop versus forward current (maximum values)

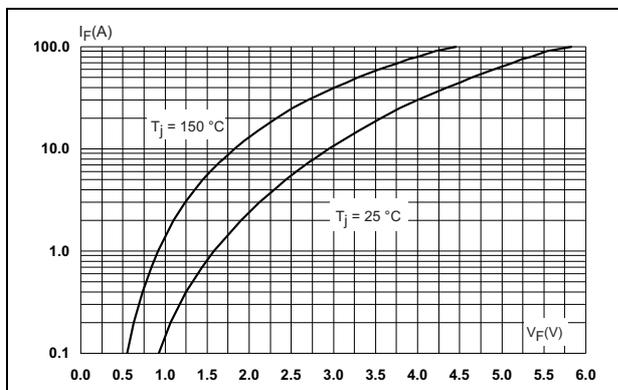


Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration

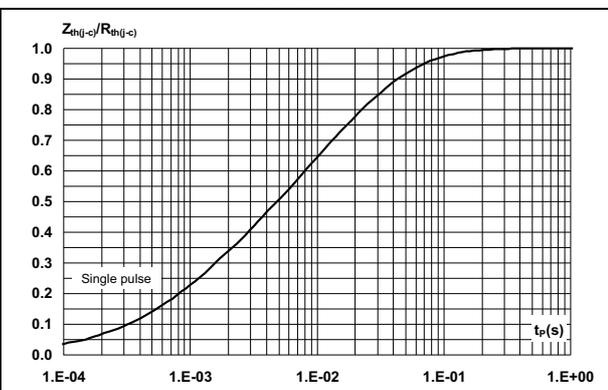


Figure 5. Peak reverse recovery current versus di_F/dt (typical values)

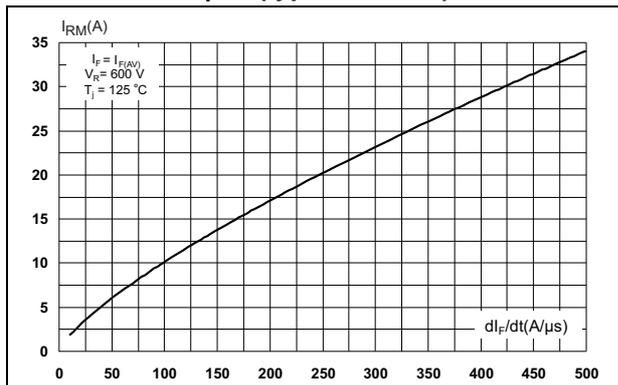


Figure 6. Reverse recovery time versus di_F/dt (typical values)

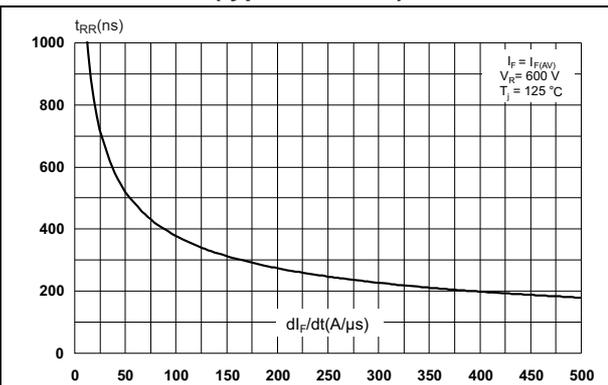


Figure 7. Reverse recovery charges versus di_F/dt (typical values)

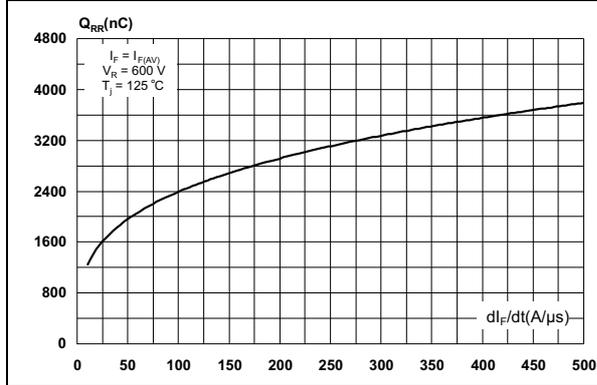


Figure 8. Reverse recovery softness factor versus di_F/dt (typical values)

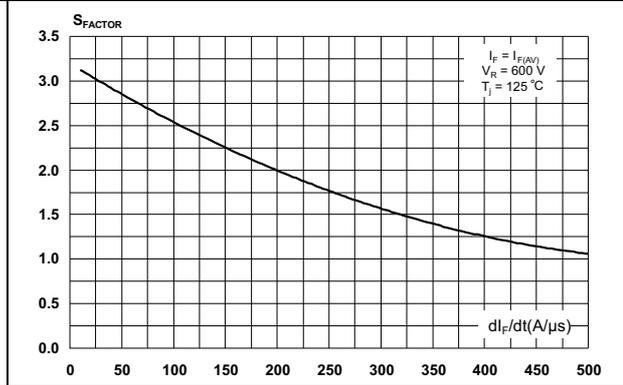


Figure 9. Relative variations of dynamic parameters versus junction temperature

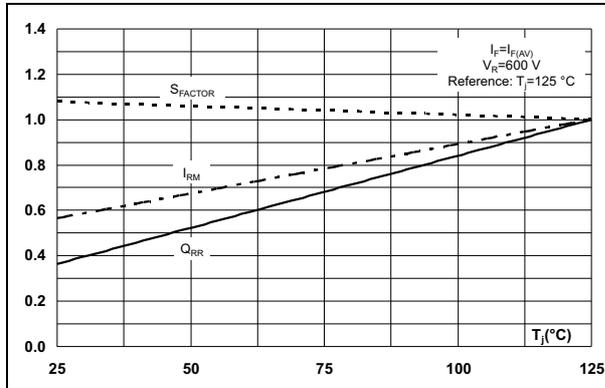


Figure 10. Junction capacitance versus reverse voltage applied (typical values)

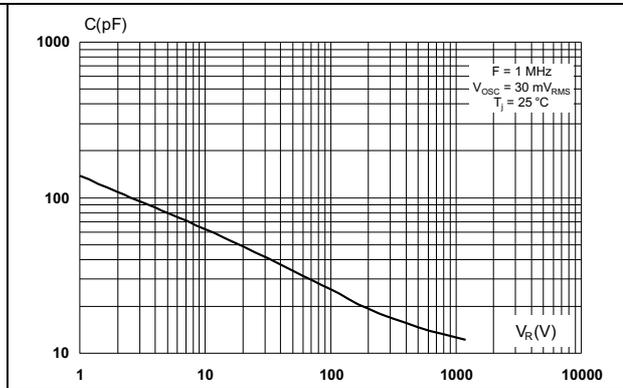


Table 6. DO-247 dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH30S12W	STTH30S12W	DO-247	4.46 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
18-Sep-2014	1	Initial release

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